NSN 5961-01-059-6780

Transistor - Page 1 of 2

View Online at https://aerobasegroup.com/nsn/5961-01-059-6780

Inclosure Material:

Ceramic

Overall Length:

Between 0.145 inches and 0.165 inches

Overall Diameter:

Between 0.355 inches and 0.375 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-117

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case and mounting hardware

Thread Size:

0.164 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

55.0 collector to base voltage/static/emitter open and 35.0 collector to emitter voltage/static/base open and 3.5 emitter to base voltage, static, collector open

Current Rating Per Characteristic:

Between 150.00 milliamperes source cutoff current and 425.00 milliamperes source cutoff current

Power Rating Per Characteristic:

5.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius case

Special Features:

Junction pattern arrangement: npn

Test Data Document:

80063-sm-a-726663 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Thread Series Designator:

Unc

Terminal Type And Quantity:

4 ribbon

Shelf Life:

N/a

Unit Of Measure:

--

Demilitarization:

No

Fiig:

A110a0